

Silicon NPN Power Transistors

BU932

DESCRIPTION

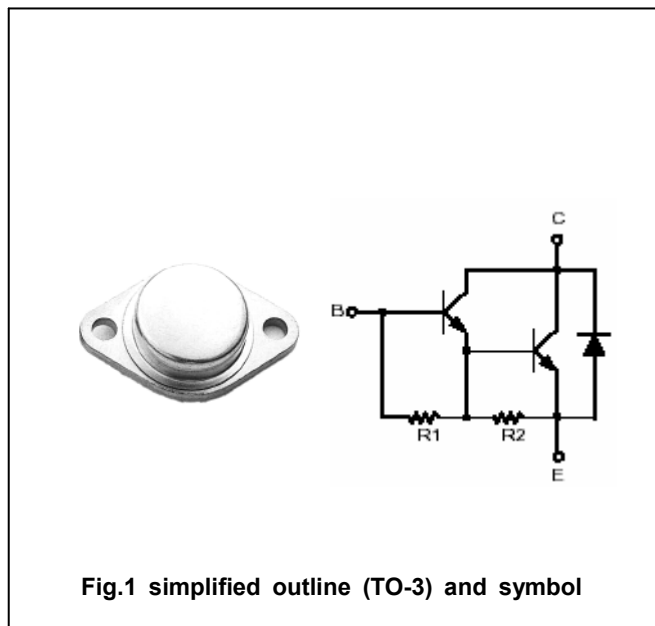
- With TO-3 package
- DARLINGTON

APPLICATIONS

- Automotive ignition applications
- Inverters circuits for motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	450	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
I_{CM}	Collector current-peak		30	A
I_B	Base current		1	A
I_{BM}	Base current-peak		5	A
P_T	Total power dissipation	$T_C \leq 25^\circ\text{C}$	150	W
T_j	Junction temperature		200	$^\circ\text{C}$
T_{stg}	Storage temperature		-40~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.0	$^\circ\text{C}/\text{W}$

Silicon NPN Power Transistors

BU932

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0	450			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =8A; I _B =150mA			1.8	V
V _{BEsat}	Base-emitter saturation voltage	I _C =8A; I _B =150mA			2.2	V
I _{CEO}	Collector cut-off current	V _{CE} =450V ; I _B =0			1.0	mA
I _{CES}	Collector cut-off current	V _{CE} =450V ; V _{BE} =0 T _C =125°C			1.0 5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			50	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =10V	300			
V _F	Diode forward voltage	I _F =10A			2.8	V

Silicon NPN Power Transistors

BU932

PACKAGE OUTLINE

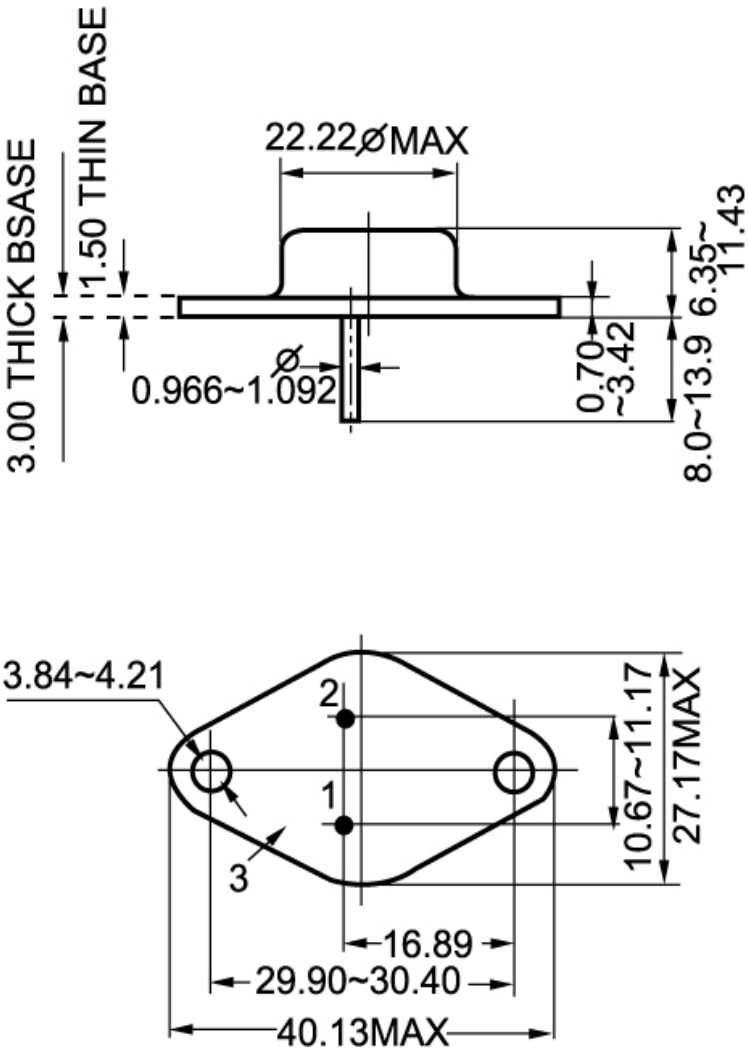


Fig.2 Outline dimensions